



Approved by:
Checked by:
Issued by:

## **SPECIFICATION**

PRODUCT: NPN 7GHz wideband transistor  
MODEL: MAS5066

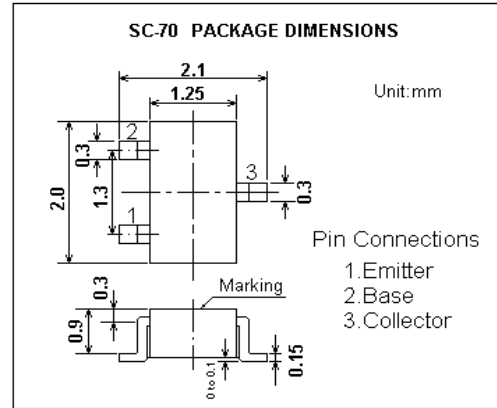
**HOPE MICROELECTRONIC CO.,LIMITED**

## FEATURES

- Low Noise Figure, High Gain
- $NF=1.1dB, |S_{21e}|^2 = 12dB (f=1GHz)$ .
- SOT-323 / SC-70 package

## APPLICATION

VHF~UHF BAND LOW NOISE AMPLIFIER



## QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$I_{CBO}$	Collector-base Current	$V_{CB}=10V, I_E=0$	-	-	1.0	$\mu A$
$I_{EBO}$	Collector-emitter Current	$V_{EB}=1V, I_C=0$	-	-	1.0	$\mu A$
$h_{FE}$	DC current gain	$I_C=10mA$ $V_{ce}=5V, T_j=25^\circ C$	80	-	240	
$f_T$	Transition frequency	$I_C=10mA, V_{ce}=5V$ $f=1GHz, T_{amb}=25^\circ C$	5	7	-	GHZ
$C_{ob}$	Output Capacitance	$V_{cb}=5V, I_E=0, f=1MHz$	-	0.7	-	pF
$C_{re}$	Reverse Transfer Capacitance	$V_{cb}=5V, I_E=0, f=1MHz$	-	0.45	0.9	pF
$ S_{21e} ^2 (1)$	Insertion Power Gain	$V_{CE}=5V, I_C=10mA,$ $f=500MHz$	-	17	-	dB
$ S_{21e} ^2 (2)$	Insertion Power Gain	$V_{CE}=5V, I_C=10mA,$ $f=1GHz$	8.5	12	-	dB
NF(1)	Noise figure	$I_C=3mA, V_{ce}=5V;$ $f=500MHz;$	--	1	-	dB
NF(2)	Noise figure	$I_C=3mA, V_{ce}=5V;$ $f=1GHz;$	-	1.1	2.0	dB

## LIMITING VALUES( $T_a=25^\circ C$ )

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
$V_{CBO}$	Collector-base voltage	Open emitter	-	20	V
$V_{CEO}$	Collector-emitter voltage	$R_{BE}=0$	-	12	V
$V_{EBO}$	Emitter-base voltage	Open collector	-	3	V
$I_C$	DC collector current		-	30	mA
$P_{tot}$	Total power dissipation	Up to $T_S = 118^\circ C$ ; note 1	-	100	mW
$T_{stg}$	Storage temperature		-55	125	$^\circ C$
$T_j$	Junction temperature		-	125	$^\circ C$

## Note

1.  $T_s$  is the temperature at the soldering point of the collector tab.

## TYPICAL CHARACTERISTICS(TA=25°C)

